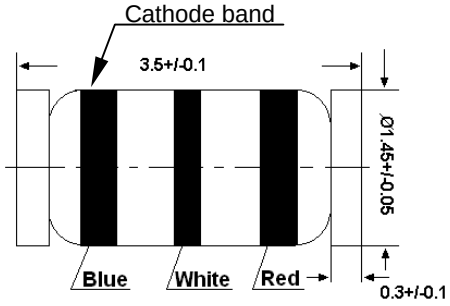
BZT52C…

SILICON PLANAR ZENER DIODES

LL-34



Glass case MiniMELF
Dimensions in mm

Features

- Ideally Suited for Automated Assembly Processes
- Total power dissipation: max. 500 mW

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	-65 to +150	°C

Characteristics at T_{amb} = 25 °C

	Symbol	Min.	Max.	Unit
Thermal Resistance Junction to Ambient Air	R_{thA}	-	305	°C/mW
Forward Voltage at I_F = 10mA	V_F	-	0.9	V

Characteristics at T_a = 25 °C

Type	Zener Voltage Range [1]			Dynamic Impedance [2]			Reverse Leakage Current		Typical Temperature coefficient at I_{ZTC} mV/°C	Test Current I_{ZTC} (mA)
	V_{znom} V	I_{ZT} for V_{ZT} mA	V	Z_{ZT} at I_{ZT} Ω (Max)	Z_{ZK} at I_{ZK} Ω (Max)	mA	I_R at V_R μA (Max)	V		
BZT52C2V4	2.4	5	2.2...2.6	100	600	1	50	1	-3.5…0	5
BZT52C2V7	2.7	5	2.5...2.9	100	600	1	20	1	-3.5…0	5
BZT52C3V0	3.0	5	2.8...3.2	95	600	1	10	1	-3.5…0	5
BZT52C3V3	3.3	5	3.1...3.5	95	600	1	5	1	-3.5…0	5
BZT52C3V6	3.6	5	3.4...3.8	90	600	1	5	1	-3.5…0	5
BZT52C3V9	3.9	5	3.7...4.1	90	600	1	3	1	-3.5…0	5
BZT52C4V3	4.3	5	4...4.6	90	600	1	3	1	-3.5…0	5
BZT52C4V7	4.7	5	4.4...5	80	500	1	3	2	-3.5…0.2	5
BZT52C5V1	5.1	5	4.8...5.4	60	480	1	2	2	-2.7…1.2	5
BZT52C5V6	5.6	5	5.2...6	40	400	1	1	2	-2…2.5	5
BZT52C6V2	6.2	5	5.8...6.6	10	150	1	3	4	0.4…3.7	5
BZT52C6V8	6.8	5	6.4...7.2	15	80	1	2	4	1.2…4.5	5
BZT52C7V5	7.5	5	7...7.9	15	80	1	1	5	2.5…5.3	5
BZT52C8V2	8.2	5	7.7...8.7	15	80	1	0.7	5	3.2…6.2	5
BZT52C9V1	9.1	5	8.5...9.6	15	100	1	0.5	6	3.8…7	5
BZT52C10	10	5	9.4...10.6	20	150	1	0.2	7	4.5…8	5
BZT52C11	11	5	10.4...11.6	20	150	1	0.1	8	5.4…9	5
BZT52C12	12	5	11.4...12.7	25	150	1	0.1	8	6…10	5
BZT52C13	13	5	12.4...14.1	30	170	1	0.1	8	7…11	5
BZT52C15	15	5	13.8...15.6	30	200	1	0.1	10.5	9.2…13	5
BZT52C16	16	5	15.3...17.1	40	200	1	0.1	11.2	10.4…14	5
BZT52C18	18	5	16.8...19.1	45	225	1	0.1	12.6	12.4…16	5
BZT52C20	20	5	18.8...21.2	55	225	1	0.1	14	14.4…18	5
BZT52C22	22	5	20.8...23.3	55	250	1	0.1	15.4	16.4…20	5
BZT52C24	24	5	22.8...25.6	70	250	1	0.1	16.8	18.4…22	5
BZT52C27	27	2	25.1...28.9	80	300	0.5	0.1	18.9	21.4…25.3	2
BZT52C30	30	2	28...32	80	300	0.5	0.1	21	24.4…29.4	2
BZT52C33	33	2	31...35	80	325	0.5	0.1	23.1	27.4…33.4	2
BZT52C36	36	2	34...38	90	350	0.5	0.1	25.2	30.4…37.4	2
BZT52C39	39	2	37...41	130	350	0.5	0.1	27.3	33.4…41.2	2

[1] V_Z is tested with pulses (20 ms).
[2] Z_Z is measured at I_Z by given a very small A.C. current signal.